



## BUL213

### HIGH VOLTAGE FAST-SWITCHING NPN POWER TRANSISTOR

- STMicroelectronics PREFERRED SALESTYPE
- NPN TRANSISTOR
- HIGH VOLTAGE CAPABILITY
- MINIMUM LOT-TO-LOT SPREAD FOR RELIABLE OPERATION
- LOW BASE-DRIVE REQUIREMENTS
- VERY HIGH SWITCHING SPEED
- FULLY CHARACTERIZED AT 125°C

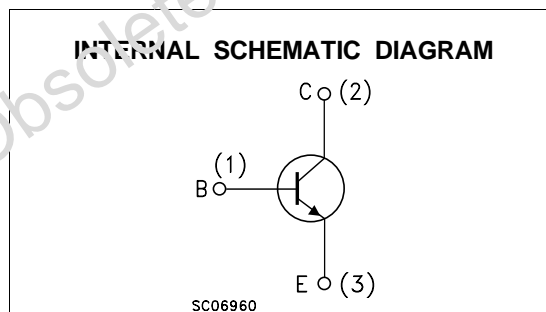
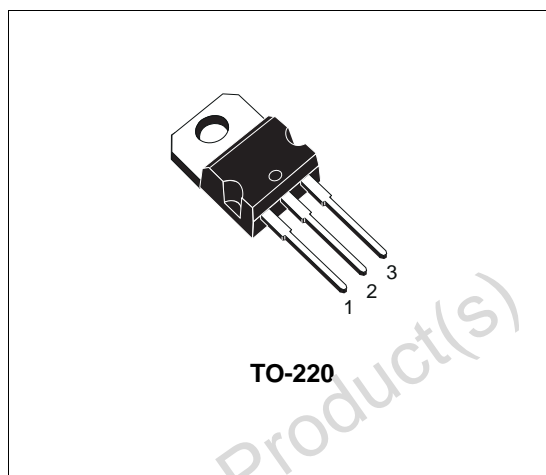
#### APPLICATIONS

- ELECTRONIC BALLASTS FOR FLUORESCENT LIGHTING
- SWITCH MODE POWER SUPPLIES

#### DESCRIPTION

The BUL213 is manufactured using high voltage Multiepitaxial Mesa technology for cost-effective high performance. It uses a Hollow Emitter structure to enhance switching speeds.

The BUL series is designed for use in lighting applications and low cost switch-mode power supplies.



#### ABSOLUTE MAXIMUM RATINGS

Symbol	Parameter	Value	Unit
$V_{CEs}$	Collector-Emitter Voltage ( $V_{BE} = 0$ )	1300	V
$V_{CE0}$	Collector-Emitter Voltage ( $I_B = 0$ )	600	V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	9	V
$I_C$	Collector Current	3	A
$I_{CM}$	Collector Peak Current ( $t_p < 5$ ms)	6	A
$I_B$	Base Current	2	A
$I_{BM}$	Base Peak Current ( $t_p < 5$ ms)	4	A
$P_{tot}$	Total Dissipation at $T_c = 25$ °C	60	W
$T_{stg}$	Storage Temperature	-65 to 150	°C
$T_j$	Max. Operating Junction Temperature	150	°C

## BUL213

### THERMAL DATA

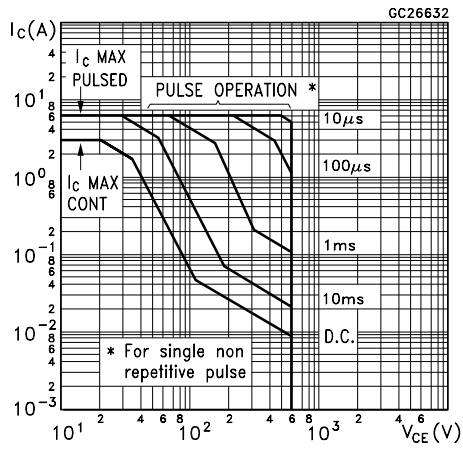
$R_{thj-case}$	Thermal Resistance Junction-Case	Max	2.08	$^{\circ}C/W$
$R_{thj-amb}$	Thermal Resistance Junction-Ambient	Max	62.5	$^{\circ}C/W$

### ELECTRICAL CHARACTERISTICS ( $T_{case} = 25^{\circ}C$ unless otherwise specified)

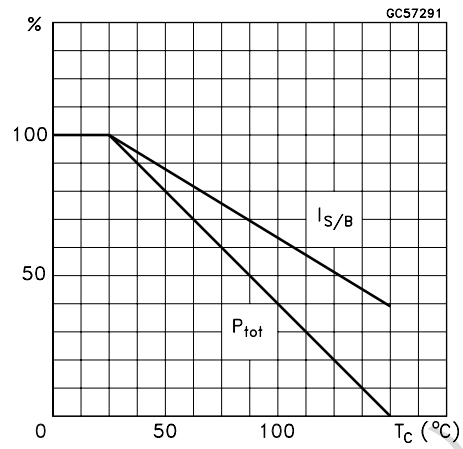
Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Unit
$I_{CES}$	Collector Cut-off Current ( $V_{BE} = 0$ )	$V_{CE} = 1300 V$ $V_{CE} = 1300 V$ $T_c = 125^{\circ}C$			100 500	$\mu A$ $\mu A$
$I_{CEO}$	Collector Cut-off Current ( $I_B = 0$ )	$V_{CE} = 600 V$			250	$\mu A$
$V_{CEO(sus)*}$	Collector-Emitter Sustaining Voltage ( $I_B = 0$ )	$I_C = 100 mA$ $L = 25 mH$	600			V
$V_{EBO}$	Emitter-Base Voltage ( $I_C = 0$ )	$I_E = 10 mA$	9			V
$V_{CE(sat)*}$	Collector-Emitter Saturation Voltage	$I_C = 0.5 A$ $I_B = 0.1 A$ $I_C = 1 A$ $I_B = 0.2 A$			0.5 0.9	V V
$V_{BE(sat)*}$	Base-Emitter Saturation Voltage	$I_C = 0.5 A$ $I_B = 0.1 A$ $I_C = 1 A$ $I_B = 0.2 A$			1.2 1.5	V V
$h_{FE*}$	DC Current Gain	$I_C = 0.35 A$ $V_{CE} = 3 V$ $I_C = 10 mA$ $V_{CE} = 5 V$	16 12		36	
$t_s$ $t_f$	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 1 A$ $V_{CL} = 400 V$ $I_{B1} = 0.2 A$ $I_{B2} = -0.4 A$ $L = 200 \mu H$		4 250	6 420	$\mu s$ ns
$t_s$ $t_f$	INDUCTIVE LOAD Storage Time Fall Time	$I_C = 1 A$ $V_{CL} = 400 V$ $I_{B1} = 0.2 A$ $I_{B2} = -0.4 A$ $L = 200 \mu H$ $T_c = 125^{\circ}C$		5.2 380		$\mu s$ ns

\* Pulsed: Pulse duration = 300  $\mu s$ , duty cycle 1.5 %

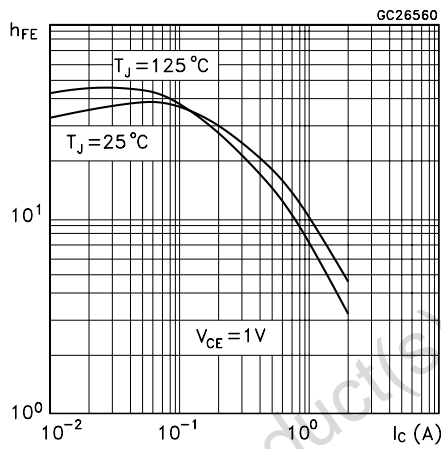
Safe Operating Areas



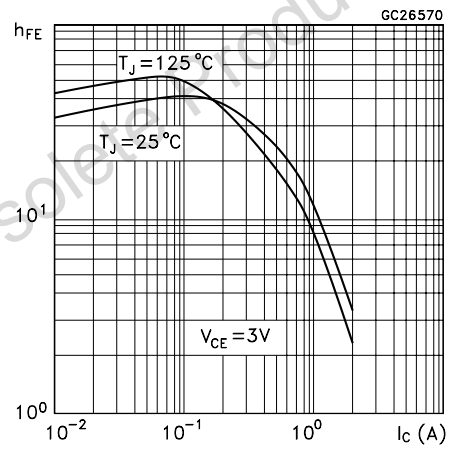
Derating Curve



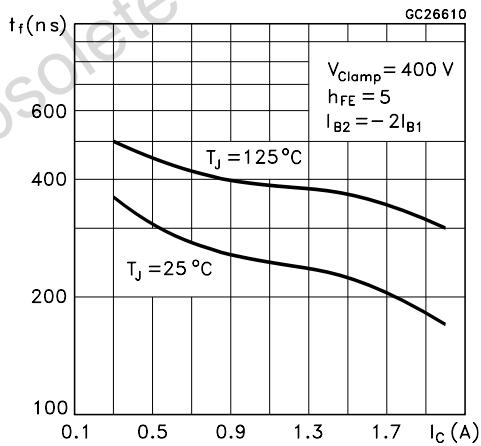
DC Current Gain



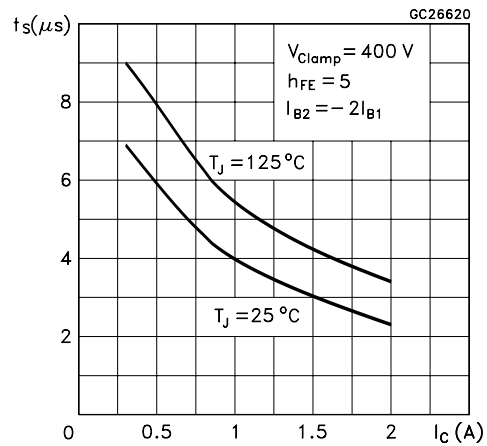
DC Current Gain



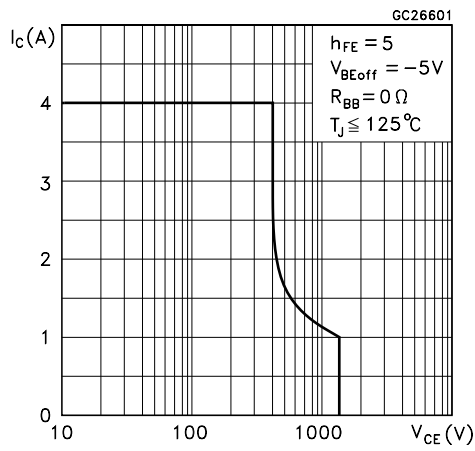
Collector Emitter Saturation Voltage



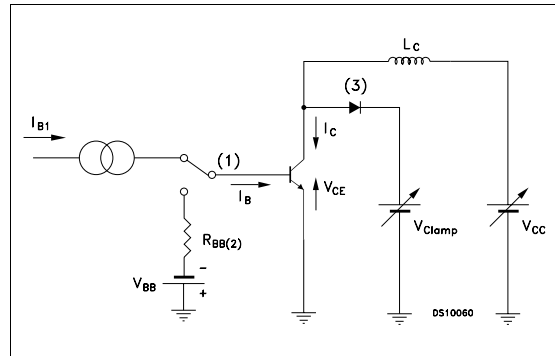
Base Emitter Saturation Voltage



Reverse Biased SOA



Inductive Load Switching Test Circuit

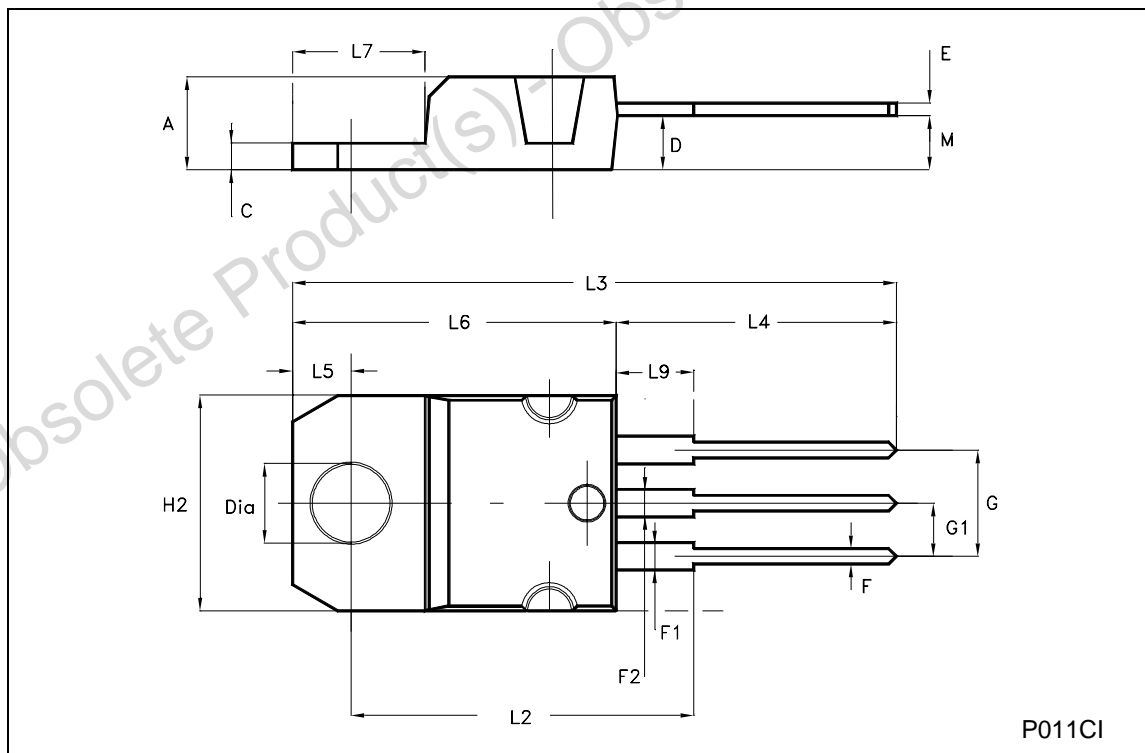


- 1) Fast electronic switch
- 2) Non-inductive Resistor
- 3) Fast recovery rectifier

Obsolete Product(s) - Obsolete Product(s)

## TO-220 MECHANICAL DATA

DIM.	mm			inch		
	MIN.	TYP.	MAX.	MIN.	TYP.	MAX.
A	4.40		4.60	0.173		0.181
C	1.23		1.32	0.048		0.052
D	2.40		2.72	0.094		0.107
E	0.49		0.70	0.019		0.027
F	0.61		0.88	0.024		0.034
F1	1.14		1.70	0.044		0.067
F2	1.14		1.70	0.044		0.067
G	4.95		5.15	0.194		0.202
G1	2.40		2.70	0.094		0.106
H2	10.00		10.40	0.394		0.409
L2		16.40			0.645	
L4	13.00		14.00	0.511		0.551
L5	2.65		2.95	0.104		0.116
L6	15.25		15.75	0.600		0.620
L7	6.20		6.60	0.244		0.260
L9	3.50		3.93	0.137		0.154
M		2.60			0.102	
DIA.	3.75		3.85	0.147		0.151



Obsolete Product(s) - Obsolete Product(s)

Information furnished is believed to be accurate and reliable. However, STMicroelectronics assumes no responsibility for the consequences of use of such information nor for any infringement of patents or other rights of third parties which may result from its use. No license is granted by implication or otherwise under any patent or patent rights of STMicroelectronics. Specification mentioned in this publication are subject to change without notice. This publication supersedes and replaces all information previously supplied. STMicroelectronics products are not authorized for use as critical components in life support devices or systems without express written approval of STMicroelectronics.

The ST logo is a trademark of STMicroelectronics

© 2003 STMicroelectronics – Printed in Italy – All Rights Reserved  
STMicroelectronics GROUP OF COMPANIES

Australia - Brazil - Canada - China - Finland - France - Germany - Hong Kong - India - Israel - Italy - Japan - Malaysia - Malta - Morocco - Singapore - Spain - Sweden - Switzerland - United Kingdom - United States.

<http://www.st.com>